

# NTLJD4150P

## Power MOSFET

-30 V, -3.4 A, Dual P-Channel, 2x2 mm WDFN Package

### Features

- WDFN 2x2 mm Package Provides Exposed Drain Pad for Excellent Thermal Conduction
- Footprint Same as SC-88 Package
- Low Profile (< 0.8 mm) for Easy Fit in Thin Environments
- Bidirectional Current Flow with Common Source Configuration
- This is a Pb-Free Device

### Applications

- Li-Ion Battery Charging and Protection Circuits
- LED Backlight, Flashlight
- Dual-High Side Load Switch

### MAXIMUM RATINGS (T<sub>J</sub> = 25°C unless otherwise noted)

Parameter		Symbol	Value	Unit	
Drain-to-Source Voltage		V <sub>DSS</sub>	-30	V	
Gate-to-Source Voltage		V <sub>GS</sub>	±20	V	
Continuous Drain Current (Note 1)	Steady State	T <sub>A</sub> = 25°C	I <sub>D</sub>	-2.7	A
			T <sub>A</sub> = 85°C	-2.0	
	t ≤ 5 s	T <sub>A</sub> = 25°C	I <sub>D</sub>	-3.4	
Power Dissipation (Note 1)	Steady State	T <sub>A</sub> = 25°C	P <sub>D</sub>	1.5	W
			t ≤ 5 s	P <sub>D</sub>	
Continuous Drain Current (Note 2)	Steady State	T <sub>A</sub> = 25°C	I <sub>D</sub>	-1.8	A
		T <sub>A</sub> = 85°C	I <sub>D</sub>	-1.4	
Power Dissipation (Note 2)	Steady State	T <sub>A</sub> = 25°C	P <sub>D</sub>	0.7	W
Pulsed Drain Current	t <sub>p</sub> = 10 μs	I <sub>DM</sub>	-14	A	
Operating Junction and Storage Temperature		T <sub>J</sub> , T <sub>STG</sub>	-55 to 150	°C	
Source Current (Body Diode) (Note 2)		I <sub>S</sub>	-1.8	A	
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)		T <sub>L</sub>	260	°C	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

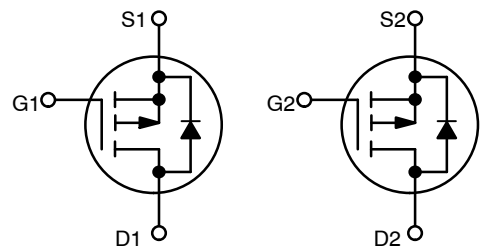
1. Surface Mounted on FR4 Board using 1 in sq pad size (Cu area = 1.127 in sq [2 oz] including traces).
2. Surface Mounted on FR4 Board using the minimum recommended pad size.



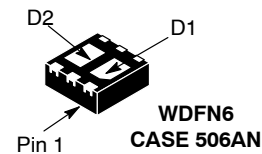
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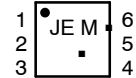
V <sub>(BR)DSS</sub>	R <sub>DS(on)</sub> Max	I <sub>D</sub> Max (Note 1)
-30 V	135 mΩ @ 10 V	-3.4 A
	200 mΩ @ 4.5 V	



P-CHANNEL MOSFET P-CHANNEL MOSFET



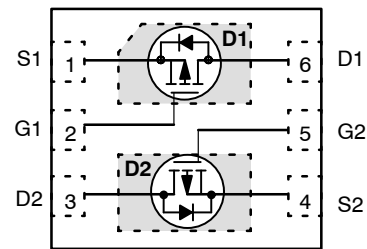
### MARKING DIAGRAM



- JE = Specific Device Code
- M = Date Code
- = Pb-Free Package

(Note: Microdot may be in either location)

### PIN CONNECTIONS



(Top View)

### ORDERING INFORMATION

Device	Package	Shipping†
NTLJD4150PTBG	WDFN6 (Pb-Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D

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## THERMAL RESISTANCE RATINGS

Parameter	Symbol	Max	Unit
<b>SINGLE OPERATION (SELF-HEATED)</b>			
Junction-to-Ambient – Steady State (Note 3)	$R_{\theta JA}$	83	°C/W
Junction-to-Ambient – Steady State Min Pad (Note 4)	$R_{\theta JA}$	177	
Junction-to-Ambient – $t \leq 5$ s (Note 3)	$R_{\theta JA}$	54	
<b>DUAL OPERATION (EQUALLY HEATED)</b>			
Junction-to-Ambient – Steady State (Note 3)	$R_{\theta JA}$	58	°C/W
Junction-to-Ambient – Steady State Min Pad (Note 3)	$R_{\theta JA}$	133	
Junction-to-Ambient – $t \leq 5$ s (Note 3)	$R_{\theta JA}$	40	

3. Surface Mounted on FR4 Board using 1 in sq pad size (Cu area = 1.127 in sq [2 oz] including traces).

4. Surface Mounted on FR4 Board using the minimum recommended pad size (30 mm<sup>2</sup>, 2 oz Cu).

## MOSFET ELECTRICAL CHARACTERISTICS ( $T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
<b>OFF CHARACTERISTICS</b>						
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = -250\ \mu\text{A}$	-30.0			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$	$I_D = -250\ \mu\text{A}$ , Ref to $25^\circ\text{C}$		1.9		mV/°C
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = -24\text{ V}, V_{GS} = 0\text{ V}$			-1.0	$\mu\text{A}$
					-5.0	
Gate-to-Source Leakage Current	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			$\pm 100$	nA

## ON CHARACTERISTICS (Note 5)

Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = -250\ \mu\text{A}$	-1.0	-1.5	-2.0	V
Gate Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$			0.4		mV/°C
Drain-to-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = -10\text{ V}, I_D = -4.0\text{ A}$		95	135	m $\Omega$
		$V_{GS} = -4.5\text{ V}, I_D = -3.0\text{ A}$		156	200	m $\Omega$
Forward Transconductance	$g_{FS}$	$V_{DS} = -10\text{ V}, I_D = -1.0\text{ A}$		1.5		S

## CHARGES, CAPACITANCES AND GATE RESISTANCE

Input Capacitance	$C_{ISS}$	$V_{GS} = 0\text{ V}, f = 1\text{ MHz}, V_{DS} = -15\text{ V}$		300		pF
Output Capacitance	$C_{OSS}$			50		
Reverse Transfer Capacitance	$C_{RSS}$			30		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = -4.5\text{ V}, V_{DS} = -15\text{ V}, I_D = -2.0\text{ A}$		3.6	4.5	nC
Threshold Gate Charge	$Q_{G(TH)}$			0.44		
Gate-to-Source Charge	$Q_{GS}$			0.79		
Gate-to-Drain Charge	$Q_{GD}$			1.54		
Gate Resistance	$R_G$			10.6		

## SWITCHING CHARACTERISTICS (Note 6)

Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = -4.5\text{ V}, V_{DD} = -24\text{ V}, I_D = -3.0\text{ A}, R_G = 2\ \Omega$		7.0		ns
Rise Time	$t_r$			16.2		
Turn-Off Delay Time	$t_{d(OFF)}$			11.8		
Fall Time	$t_f$			8.8		

5. Pulse Test: Pulse Width  $\leq 300\ \mu\text{s}$ , Duty Cycle  $\leq 2\%$ .

6. Switching characteristics are independent of operating junction temperatures.

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## MOSFET ELECTRICAL CHARACTERISTICS ( $T_J = 25^\circ\text{C}$ unless otherwise noted) (continued)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit	
<b>DRAIN-SOURCE DIODE CHARACTERISTICS</b>							
Forward Recovery Voltage	$V_{SD}$	$V_{GS} = 0\text{ V},$ $I_S = -2.0\text{ A}$	$T_J = 25^\circ\text{C}$		-0.85	-1.0	V
			$T_J = 85^\circ\text{C}$		-0.77		
Reverse Recovery Time	$t_{RR}$	$V_{GS} = 0\text{ V}, d_{ISD}/d_t = 100\text{ A}/\mu\text{s},$ $I_S = -2.0\text{ A}$			8.9		ns
Charge Time	$t_a$				6.2		
Discharge Time	$t_b$				2.9		
Reverse Recovery Time	$Q_{RR}$				3.0		

5. Pulse Test: Pulse Width  $\leq 300\ \mu\text{s}$ , Duty Cycle  $\leq 2\%$ .
6. Switching characteristics are independent of operating junction temperatures.

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## TYPICAL PERFORMANCE CURVES ( $T_J = 25^\circ\text{C}$ unless otherwise noted)

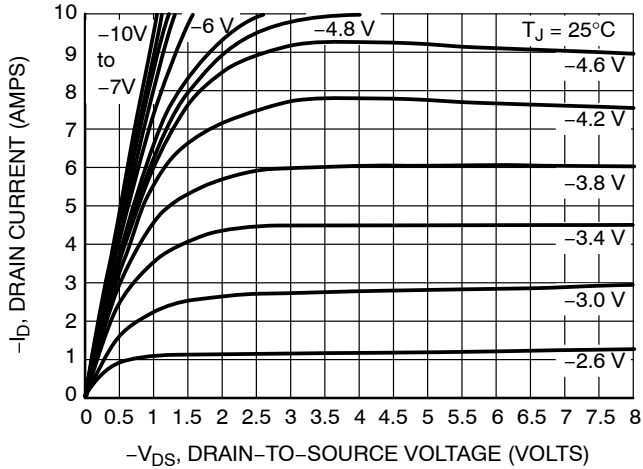


Figure 1. On-Region Characteristics

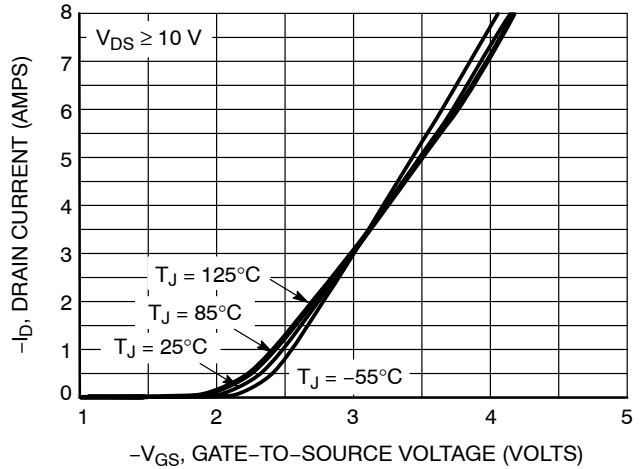


Figure 2. Transfer Characteristics

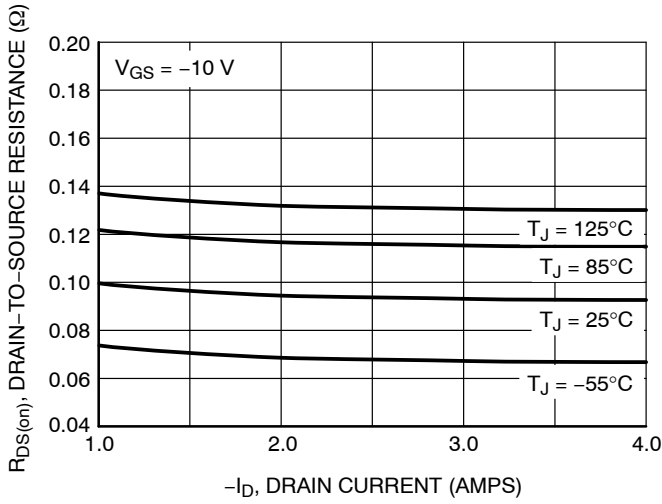


Figure 3. On-Resistance versus Drain Current

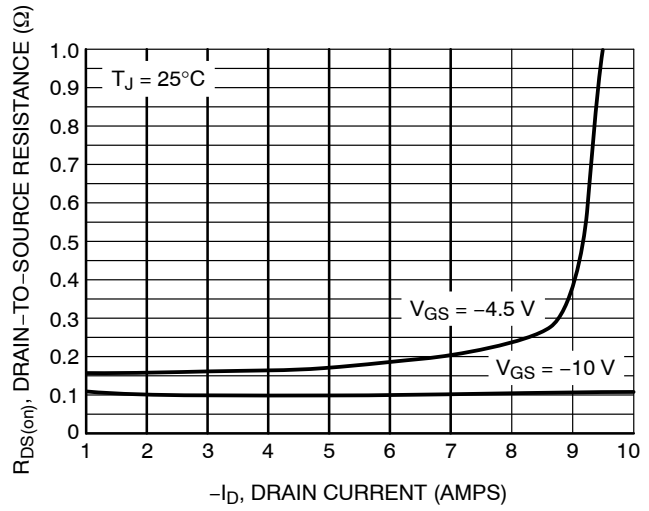


Figure 4. On-Resistance versus Drain Current and Gate Voltage

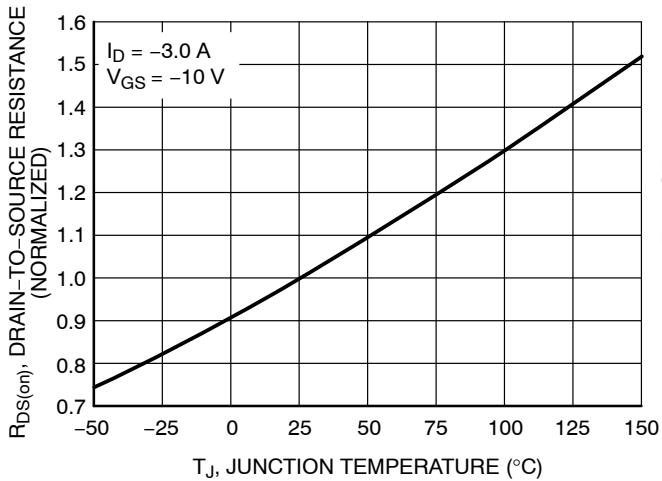


Figure 5. On-Resistance Variation with Temperature

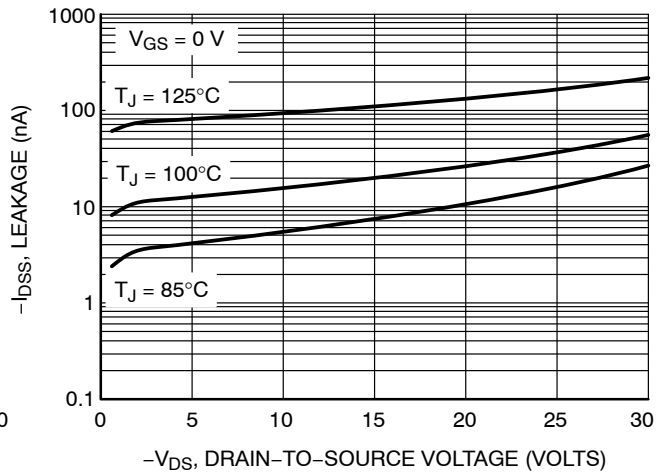


Figure 6. Drain-to-Source Leakage Current versus Voltage

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## TYPICAL PERFORMANCE CURVES ( $T_J = 25^\circ\text{C}$ unless otherwise noted)

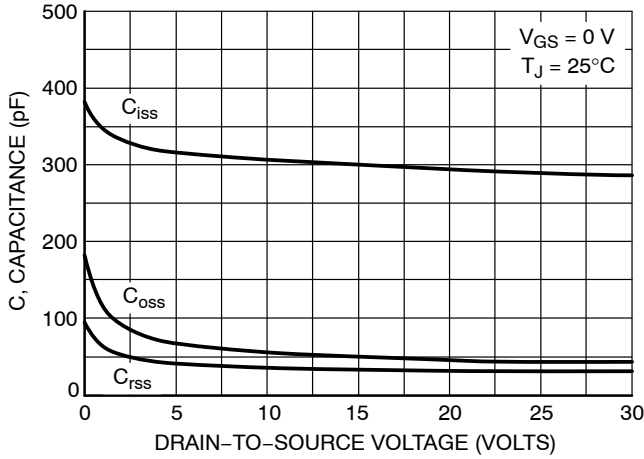


Figure 7. Capacitance Variation

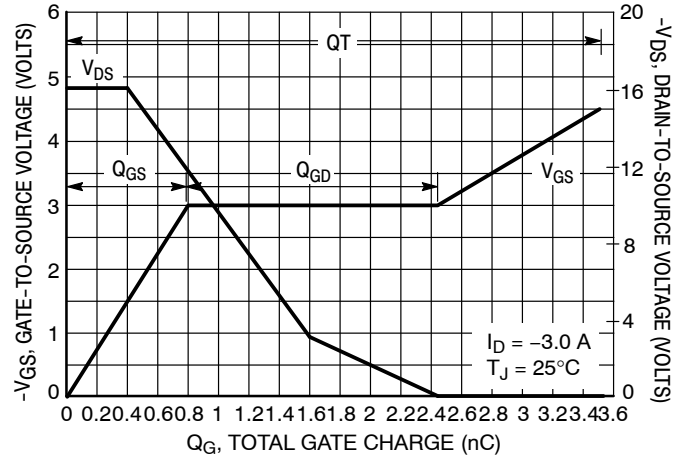


Figure 8. Gate-To-Source and Drain-To-Source Voltage versus Total Charge

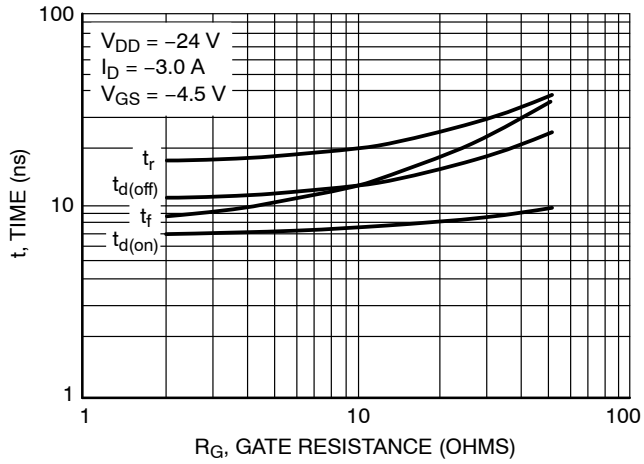


Figure 9. Resistive Switching Time Variation versus Gate Resistance

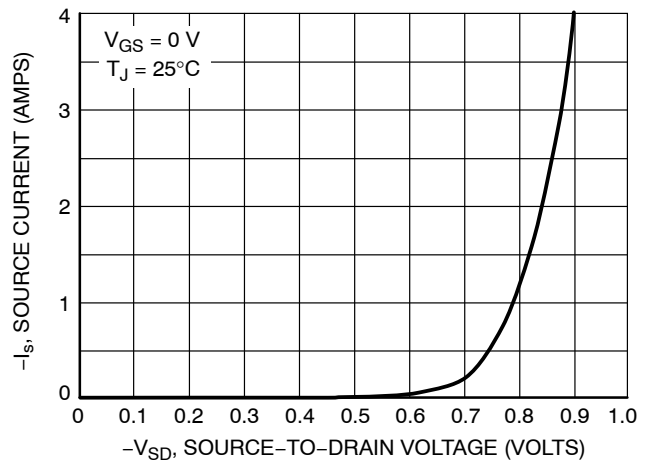


Figure 10. Diode Forward Voltage versus Current

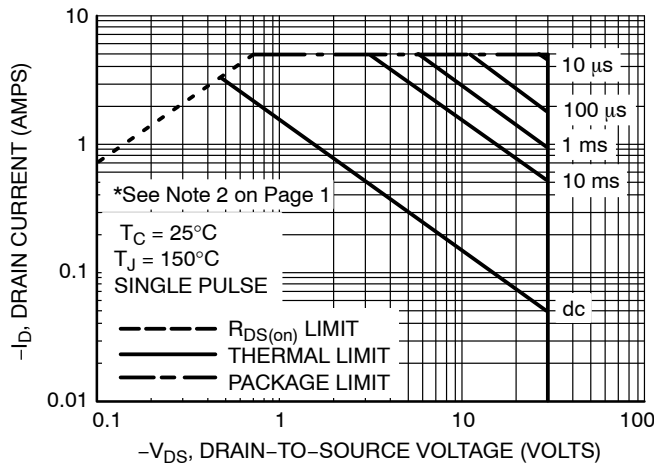


Figure 11. Maximum Rated Forward Biased Safe Operating Area

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## TYPICAL PERFORMANCE CURVES ( $T_J = 25^\circ\text{C}$ unless otherwise noted)

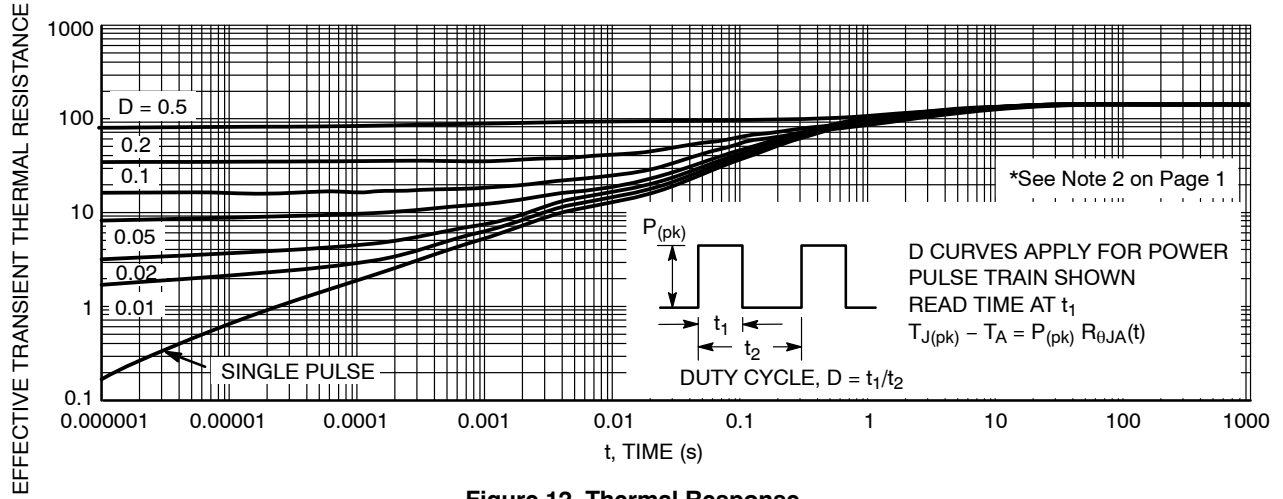
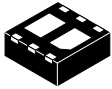


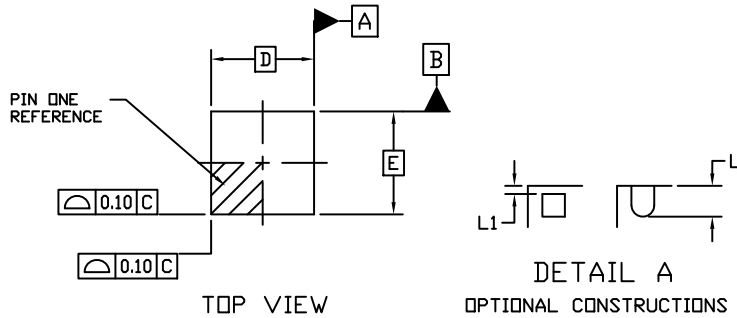
Figure 12. Thermal Response

# MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS



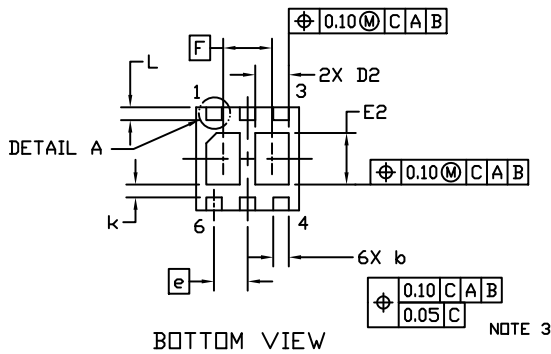
WDFN6 2x2, 0.65P  
CASE 506AN  
ISSUE H

DATE 25 JAN 2022



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS
3. DIMENSION *b* APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.30 MM FROM THE TERMINAL TIP.
4. COPLANARITY APPLIES TO THE EXPOSED PADS AS WELL AS THE TERMINALS.



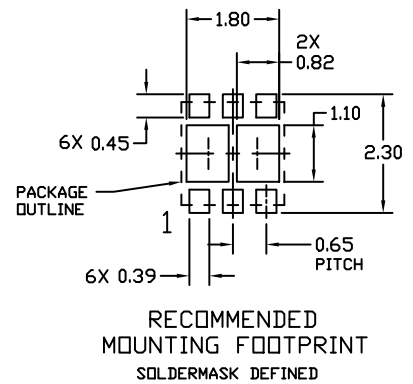
DIM	MILLIMETERS	
	MIN.	MAX.
A	0.70	0.80
A1	0.00	0.05
A3	0.20 REF	
<i>b</i>	0.25	0.35
D	2.00 BSC	
D2	0.57	0.77
E	2.00 BSC	
E2	0.90	1.10
<i>e</i>	0.65 BSC	
F	0.95 BSC	
<i>k</i>	0.25 REF	
L	0.20	0.30
L1	---	0.10

GENERIC MARKING DIAGRAM\*



XX = Specific Device Code  
M = Date Code

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.



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DESCRIPTION:	WDFN6 2x2, 0.65P	PAGE 1 OF 1

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